

L Number	Hits	Search Text	DB	Time stamp
1	2	(("5699375") or ("5963568")).PN.	USPAT	2003/03/07 13:38
2	2	active and (((("5699375") or ("5963568")).PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 13:38
	0	(plurality near2 semiconductor near2 resonat\$4) and 372/\$ and group adj V	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 13:36
	3	(plurality near semiconductor near resonat\$5) and 372/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 16:03
	734	(semiconductor near3 resonat\$5) and 372/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 09:17
	15	(semiconductor near2 resonat\$4) and 372/\$ and group adj V	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 16:05
	222	((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 16:39
	11	((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) or groove)) and ((semiconductor near2 resonat\$4) and 372/\$ and group adj V)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 16:07
	35	((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) and groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 16:40
	70	((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) or (stripe near shaped near groove))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 16:40
	3	((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) and (stripe near shaped near groove))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:01
	1	((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) and (stripe near shaped near groove))) and group adj V	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 16:44

	7	((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) and groove)) and group adj V	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 16:45
	11	((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) or (stripe near shaped near groove)) and group adj V	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:54
	4	((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) and (stripe near groove))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:01
	28	((semiconductor near3 resonat\$5) and 372/\$) and ((high and low) near resistance) or (stripe near shaped near groove))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:01
	0	((semiconductor near3 resonat\$5) and 372/\$) and ((high and low) near resistance) and (stripe near shaped near groove))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:01
	70	((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) or (stripe near shaped near groove))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:02
	0	(semiconductor near3 resonat\$5) and 372/\$ and (high near resistance) and (low near resistance) and (stripe near shaped near groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:03
	17	(semiconductor near3 resonat\$5) and 372/\$ and (stripe near shaped near groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:03
	24	(semiconductor near3 resonat\$5) and 372/\$ and (stripe near groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:03
	201	(semiconductor near3 resonat\$5) and 372/\$ and (groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:03
	29	(semiconductor near3 resonat\$5) and 372/\$ and (groove) and (resistan\$5 near (region or layer or film or medium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:20
	29	(semiconductor near3 resonat\$5) and 372/\$ and (groove or (stripe near groove) or (shaped near groove)) and (resistan\$5 near (region or layer or film or medium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:22

	15	((semiconductor near3 resonat\$5) and 372/\$ and (groove or (stripe near groove) or (shaped near groove)) and (resistan\$5 near (region or layer or film or medium))) and (group near V)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:56
	4	((semiconductor near3 resonat\$5) and 372/\$ and (groove or (stripe near groove) or (shaped near groove)) and (resistan\$5 near (region or layer or film or medium))) and (group near V)) and infrared	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 10:19
	3	((((semiconductor near3 resonat\$5) and 372/\$ and (groove or (stripe near groove) or (shaped near groove)) and (resistan\$5 near (region or layer or film or medium))) and (group near V)) and infrared) and (refractive near (index or indice or indec))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 09:59
	0	((semiconductor near3 resonat\$5) and 372/\$ and (groove or (stripe near groove) or (shaped near groove)) and (resistan\$5 near (region or layer or film or medium))) and (air near gap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 10:01
	3	((semiconductor near3 resonat\$5) and 372/\$ and (groove)) and (air near gap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 10:19
	78	((semiconductor near3 resonat\$5) and 372/\$ and (groove)) and (insulat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 10:57
	4	((semiconductor near3 resonat\$5) and 372/\$ and (groove)) and (electrical\$4 near insulat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 10:12
	1	((semiconductor near3 resonat\$5) and 372/\$ and (groove)) and (groove near insulat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 10:12
	0	((((semiconductor near3 resonat\$5) and 372/\$ and (groove)) and (groove near insulat\$4)) and infrared) and (air near gap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 10:20
	1	((semiconductor near3 resonat\$5) and 372/\$ and (groove)) and (groove near insulat\$4)) and infrared	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 12:44
	0	((semiconductor near3 resonat\$5) and 372/\$ and (groove)) and dc and dvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/19 12:44
	6	((semiconductor near3 resonat\$5) and 372/\$ and (groove)) and (insulat\$4) and (cd or dvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/21 16:56

	0	((semiconductor near3 resonat\$5) and 372/\$ and (groove) and (insulat\$4) and (cd AND dvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/21 16:57
	484	(VCSEL or (vertical near cavity near surface near emit\$5 near laser) or (semiconductor near laser)) same (material near3 different)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 11:06
	245	(VCSEL or (vertical near cavity near surface near emit\$5 near laser) or (semiconductor near laser)) WITH (material near3 different)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 11:07
	213	((VCSEL or (vertical near cavity near surface near emit\$5 near laser) or (semiconductor near laser)) same (material near3 different)) and (Gallium or photons)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 11:07
	29	((VCSEL or (vertical near cavity near surface near emit\$5 near laser) or (semiconductor near laser)) same (material near3 different)) and (Gallium or photons) and red and infrared	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 11:07
	105	((VCSEL or (vertical near cavity near surface near emit\$5 near laser) or (semiconductor near laser)) WITH (material near3 different)) and (Gallium or photons)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 11:07
	19	((VCSEL or (vertical near cavity near surface near emit\$5 near laser) or (semiconductor near laser)) WITH (material near3 different)) and (Gallium or photons) and red and infrared	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 11:24
	7	((VCSEL or (vertical near cavity near surface near emit\$5 near laser) or (semiconductor near laser)) WITH (material near3 different)) and ((Gallium near ion) or photons) and red and infrared	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 11:25
	60	(semiconductor near3 resonat\$5) and 372/\$ and ((different or (non adj similar) or dissimilar or other or ohterwose or unalike or unlike or unequal or unsimilar or various) near material)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 09:26
	0	((semiconductor near3 resonat\$5) and 372/\$ and ((different or (non adj similar) or dissimilar or other or ohterwose or unalike or unlike or unequal or unsimilar or various) near material)) and (red and infrared) and (protons or gallium) and (air near2 gap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 09:29
	4	((semiconductor near3 resonat\$5) and 372/\$ and ((different or (non adj similar) or dissimilar or other or ohterwose or unalike or unlike or unequal or unsimilar or various) near material)) and (red and infrared) and (protons or gallium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 09:48
	4	((semiconductor near3 resonat\$5) and 372/\$ and ((different or (non adj similar) or dissimilar or other or ohterwose or unalike or unlike or unequal or unsimilar or various) near material)) and (red and infrared) and (protons or gallium)) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 09:48

	7216	((plurality or more or multi\$4 or two) near laser) and active	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 11:03
	62	((plurality ro multi\$4 or more or two) near2 semiconductor near2 resonat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 11:07
	796	((plurality or more or multi\$4 or two) near laser near semiconductor) and active	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 11:06
	26	((plurality ro multi\$4 or more or two) near2 semiconductor near2 resonat\$4)) and active and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 11:07